

N- Channel 30-V (D-S) MOSFET

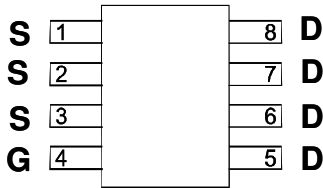
General Description

The B3450 is the N-Channel logic enhancement mode power field effect transistors are produced using high cell density, DMOS trench technology. This high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage application such as cellular phone and notebook computer power management and other battery powered circuits where high-side switching and low in-line power loss are needed in a very small outline surface mount package.

Features

- $R_{DS(ON)}=28m\Omega@V_{GS}=10V$
- $R_{DS(ON)}=42m\Omega@V_{GS}=4.5V$
- **Super High Density Cell Design for Extremely Low $R_{DS(ON)}$**
- **Exceptional On-Resistance and Maximum DC Current**
- **SOP-8 Package**

Pin Configuration



Applications

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch
- DSC

Absolute Maximum Ratings (TA=25°C Unless Otherwise Noted):

Parameter	Symbol	N-Channel	Unit
Drain-Source Voltage	V_{DSS}	30	V
Gate-Source Voltage	V_{GSS}	± 20	V
Continuous Drain Current (t _J =150°C)	I_D	TA=25°C	6.9
		TA=70°C	5.8
Pulsed Drain Current	I_{DM}	30	A
Maximum Power Dissipation	P_D	TA=25°C	2.0
		TA=70°C	1.3
Operating Junction Temperature	T_J	-55 to 150	°C
Thermal Resistance-Junction to Case	$R_{\theta JC}$	48	°C/W